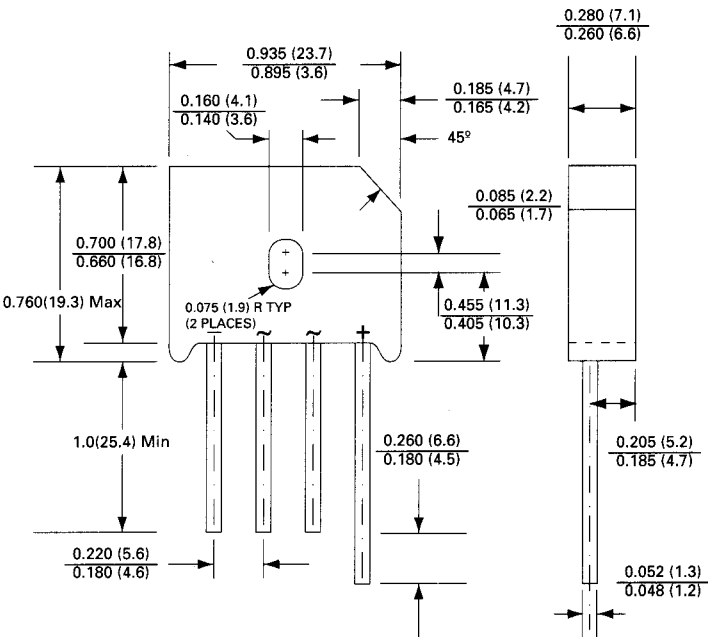


KBU4A ...KBU4M; KBU6A ...KBU6M; KBU8A ...KBU8M
4.0A/6.0A/8.0A SINGLE - PHASE SILICON BRIDGE

Features

- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- Plastic material has Underwriters Laboratory Flammability Classification 94V-0.
- Surge overload rating - 200 amperes peak
- Mounting Position: Any
- Mounting Torque: 5 In. lb. max
- U/L recognized file # 142814

VOLTAGE RANGE
50 to 1000 Volts
CURRENT
4.0/6.0/8.0 Amperes

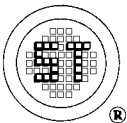


Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless specified Resistive or inductive load,60 Hz.
For capacitive load, derate current by 20%.

	KBU4A	KBU4B	KBU4D	KBU4G	KBU4J	KBU4K	KBU4M	
	KBU6A	KBU6B	KBU6D	KBU6G	KBU6J	KBU6K	KBU6M	
	KBU8A	KBU8B	KBU8D	KBU8G	KBU8J	KBU8K	KBU8M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Max RMS Bridge Input Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Output Current at $T_C = 100\text{ }^{\circ}\text{C}$ $T_A = 50\text{ }^{\circ}\text{C}/40\text{ }^{\circ}\text{C}/45\text{ }^{\circ}\text{C}$	KBU4	40 40	KBU6	60 60	KBU8	80 60	A A	
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC medthod)		200		250		300	A	
Maximum Instantaneous Forward Voltage Drop per element at 3.0A/3.0A/8.0A		1.0		1.0		1.0	V	
Maximum Reverse Leakage at rated $T_A = 25\text{ }^{\circ}\text{C}$ DC Block Voltage per element $T_C = 100\text{ }^{\circ}\text{C}$		10 100		10 200		10 300	μA mA	
Operating and storage temperature Range, T_J, T_{STG}		-65 to + 150						



SEMTECH ELECTRONICS LTD.
(wholly owned subsidiary of HONEY TECHNOLOGY LTD.)



KBU4A ...KBU4M; KBU6A ...KBU6M; KBU8A ...KBU8M

4.0A/6.0A/8.0A SINGLE - PHASE SILICON BRIDGE

RATING AND CHARACTERISTICS CURVES

KBU4/6/8 SERIES

FIG. 1-DERATING CURVE FOR
OUTPUT RECTIFIED CURRENT

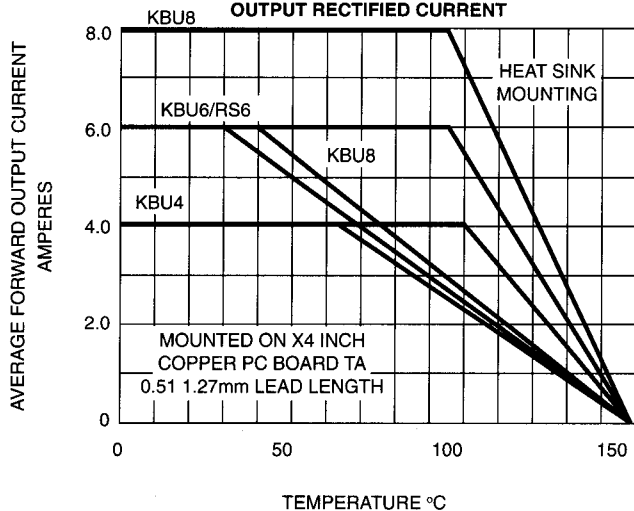


FIG. 2-TYPICAL INSTANTANEOUS FORWARD
CHARACTERISTICS

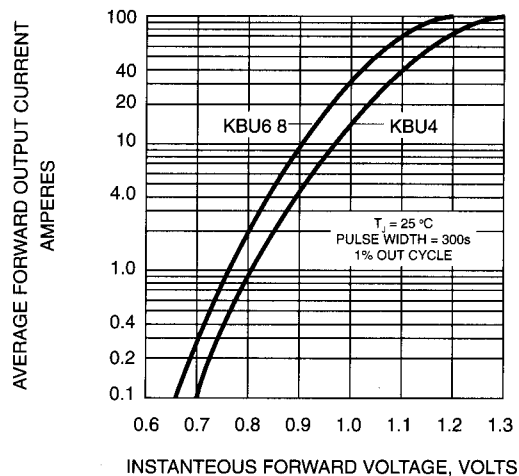


FIG. 3-MAXIMUN NON RETETITIVE PEAK
FORWARD SURGE CURRENT

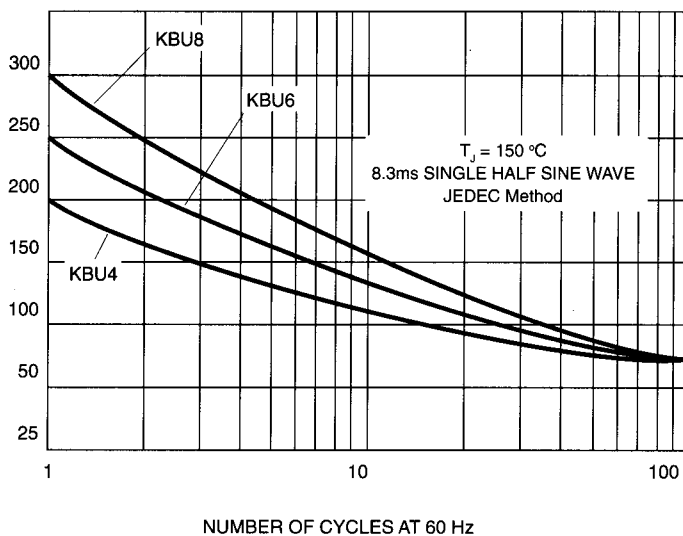


FIG. 4-TYPICAL REVERSE
CHARACTERISTICS

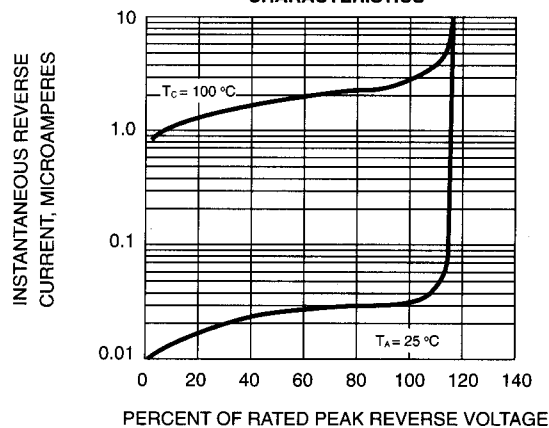
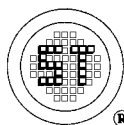
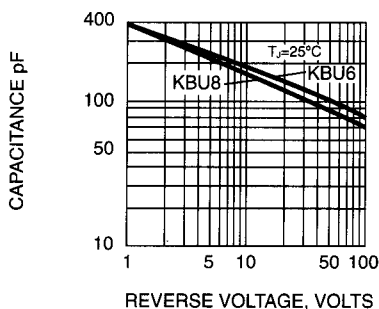
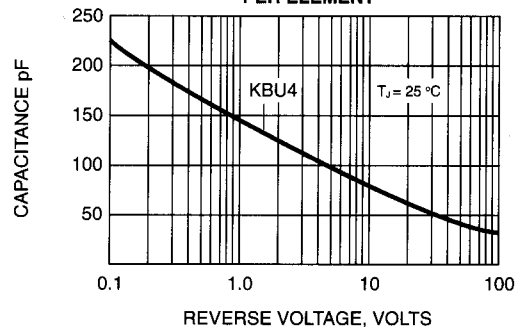


FIG. 5-TYPICAL JUNCTION CAPACITANCE
PER ELEMENT



SEMTECH ELECTRONICS LTD.
(wholly owned subsidiary of HONEY TECHNOLOGY LTD.)

